74LVCH32244A

32-bit buffer/line driver; 5 V input/output tolerant; 3-state

Rev. 3 — 16 December 2011 Product data sheet

1. General description

The 74LVCH32244A is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families. Inputs can be driven from either 3.3 V or 5.0 V devices. In 3-state operation outputs can handle 5 V. These features allow the use of these devices as translators in a mixed 3.3 V and 5 V environment.

The 74LVCH32244A is a 32-bit non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by eight output enable outputs (1$\overline{OE}$ to 8$\overline{OE}$). A HIGH on pin n$\overline{OE}$ causes the outputs to assume a high-impedance OFF-state.

To ensure the high-impedance state during power-up or power-down, pin n$\overline{OE}$ should be tied to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Bus hold on data inputs eliminates the need for external pull-up resistors to hold unused or floating data inputs at a valid logic level.

2. Features and benefits

- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 3.6 V
- CMOS low-power consumption
- MULTIBYTE flow-through standard pinout architecture
- Low inductance multiple power and ground pins for minimum noise and ground bounce
- Direct interface with TTL levels
- Inputs accept voltages up to 5.5 V
- All data inputs have bus hold
- Complies with JEDEC standard:
  - JESD8-7A (1.65 V to 1.95 V)
  - JESD8-5A (2.3 V to 2.7 V)
  - JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-B exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Specified from −40 °C to +85 °C
- Packaged in plastic fine-pitch ball grid array package

3. Ordering information

Table 1: Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC32244AEC	−40 °C to +85 °C	LFBGA96	plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 × 5.5 × 1.05 mm	SOT536-1

4. Functional diagram

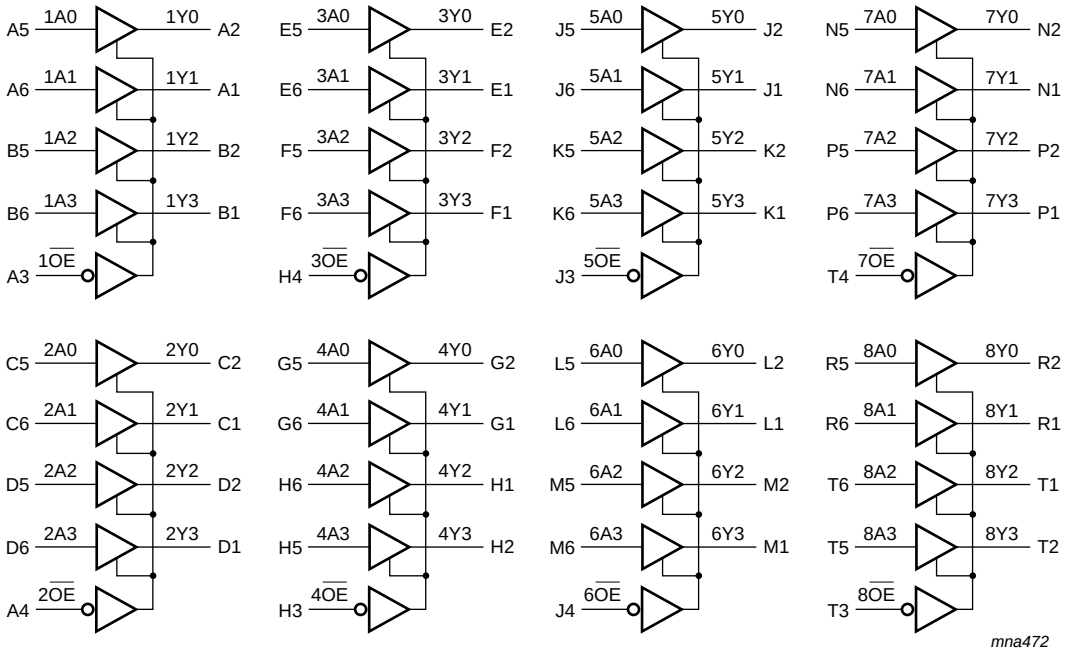


Fig 1. Logic symbol

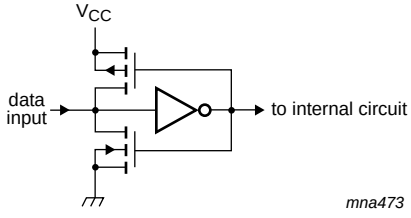


Fig 2. Bus hold circuit

5. Pinning information

5.1 Pinning

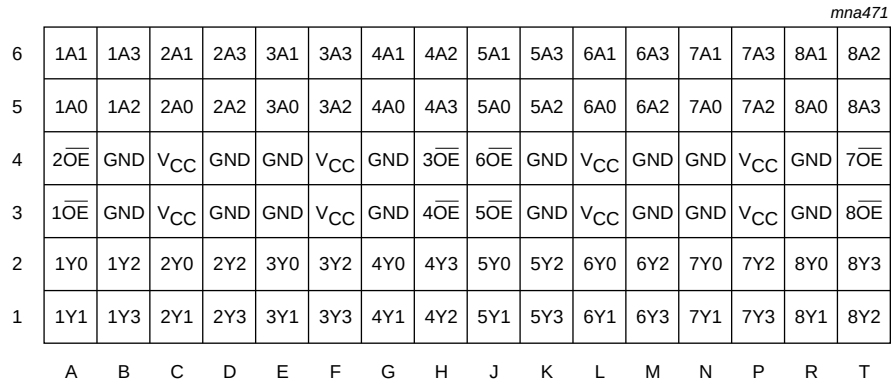


Fig 3. Pin configuration

5.2 Pin description

Table 2: Pin description

Symbol	Ball	Description
n$\overline{OE}$ (n = 1 to 8)	A3, A4, H4, H3, J3, J4, T4, T3	3-state output enable input (active LOW)
1A[0:7]	A5, A6, B5, B6	data input
2A[0:7]	C5, C6, D5, D6	
3A[0:7]	E5, E6, F5, F6	
4A[0:7]	G5, G6, H6, H5	
5A[0:7]	J5, J6, K5, K6	
6A[0:7]	L5, L6, M5, M6	
7A[0:7]	N5, N6, P5, P6	
8A[0:7]	R5, R6, T6, T5	
1Y[0:7]	A2, A1, B2, B1	data output
2Y[0:7]	C2, C1, D2, D1	
3Y[0:7]	E2, E1, F2, F1	
4Y[0:7]	G2, G1, H1, H2	
5Y[0:7]	J2, J1, K2, K1	
6Y[0:7]	L2, L1, M2, M1	
7Y[0:7]	N2, N1, P2, P1	
8Y[0:7]	R2, R1, T1, T2	
GND	B3, B4, D3, D4, E3, E4, G3, G4, K3, K4, M3, M4, N3, N4, R3, R4	ground (0 V)
V_{CC}	C3, C4, F3, F4, L3, L4, P3, P4	supply voltage

6. Functional description

Table 3: Functional table[1]

Input		Output
$n\overline{OE}$	nAn	nYn
L	L	L
L	H	H
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$		−50	-	mA
V_I	input voltage		[1]	−0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$		-	±50	mA
V_O	output voltage	output HIGH or LOW state	[2]	−0.5	V_{CC} + 0.5	V
		output 3-state	[2]	−0.5	+6.5	V
I_O	output current	V_O = 0 V to V_{CC}		-	±50	mA
I_{CC}	supply current		[3]	-	200	mA
I_{GND}	ground current		[3]	−200	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	T_{amb} = −40 °C to +125 °C	[4]	-	1000	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] All supply and ground pins connected externally to one voltage source.

[4] Above 70 °C the value of P_{tot} derate linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	3.6	V
		functional	1.2	-	-	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	output HIGH or LOW state	0	-	V_{CC}	V
		output 3-state	0	-	5.5	V
T_{amb}	ambient temperature	in free air	−40	-	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V_{CC} = 2.7 V to 3.6 V	-	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.2 V	1.08	-	-	1.08	-	V
		V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	-	-	0.65 × V_{CC}	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.2 V	-	-	0.12	-	0.12	V
		V_{CC} = 1.65 V to 1.95 V	-	-	0.35 × V_{CC}	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = –100 μA; V_{CC} = 1.65 V to 3.6 V	V_{CC} – 0.2	-	-	V_{CC} – 0.3	-	V
		I_O = –4 mA; V_{CC} = 1.65 V	1.2	-	-	1.05	-	V
		I_O = –8 mA; V_{CC} = 2.3 V	1.8	-	-	1.65	-	V
		I_O = –12 mA; V_{CC} = 2.7 V	2.2	-	-	2.05	-	V
		I_O = –18 mA; V_{CC} = 3.0 V	2.4	-	-	2.25	-	V
		I_O = –24 mA; V_{CC} = 3.0 V	2.2	-	-	2.0	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 100 μA; V_{CC} = 1.65 V to 3.6 V	-	-	0.2	-	0.3	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.45	-	0.65	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.6	-	0.8	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.4	-	0.6	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.55	-	0.8	V
I_I	input leakage current [2]	V_{CC} = 3.6 V; V_I = 5.5 V or GND	-	±0.1	±5	-	±20	μA
I_{OZ}	OFF-state output current [2]	V_I = V_{IH} or V_{IL}; V_{CC} = 3.6 V; V_O = 5.5 V or GND;	-	0.1	±5	-	±20	μA
I_{OFF}	power-off leakage supply	V_{CC} = 0 V; V_I or V_O = 5.5 V	-	0.1	±10	-	±20	μA
I_{CC}	supply current	V_{CC} = 3.6 V; V_I = V_{CC} or GND; I_O = 0 A	-	0.1	40	-	160	μA
ΔI_{CC}	additional supply current	per input pin; V_{CC} = 2.7 V to 3.6 V; V_I = V_{CC} – 0.6 V; I_O = 0 A	-	5	500	-	5000	μA
C_I	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND to V_{CC}	-	5.0	-	-	-	pF
I_{BHL}	bus hold LOW current [3][4]	V_{CC} = 1.65; V_I = 0.58 V	10	-	-	10	-	μA
		V_{CC} = 2.3; V_I = 0.7 V	30	-	-	25	-	μA
		V_{CC} = 3.0; V_I = 0.8 V	75	-	-	60	-	μA

Table 6. Static characteristics *…continued*

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
I_{BHH}	bus hold HIGH current [3][4]	V_{CC} = 1.65; V_I = 1.07 V	–10	-	-	–10	-	µA
		V_{CC} = 2.3; V_I = 1.7 V	–30	-	-	–25	-	µA
		V_{CC} = 3.0; V_I = 2.0 V	–75	-	-	–60	-	µA
I_{BHLO}	bus hold LOW overdrive current [3][5]	V_{CC} = 1.95 V	200	-	-	200	-	µA
		V_{CC} = 2.7 V	300	-	-	300	-	µA
		V_{CC} = 3.6 V	500	-	-	500	-	µA
I_{BHHO}	bus hold HIGH overdrive current [3][5]	V_{CC} = 1.95 V	–200	-	-	–200	-	µA
		V_{CC} = 2.7 V	–300	-	-	–300	-	µA
		V_{CC} = 3.6 V	–500	-	-	–500	-	µA

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

[2] The bus hold circuit is switched off when $V_I > V_{CC}$ allowing 5.5 V on the input pin.

[3] Valid for data inputs only. Control inputs do not have a bus hold circuit.

[4] The specified sustaining current at the data inputs holds the input below the specified V_I level.

[5] The specified overdrive current at the data input forces the data input to the opposite logic input state.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 6.

Symbol	Parameter	Conditions	T_{amb} = –40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	nAn to nYn; see Figure 4 [2]						
		V_{CC} = 1.2 V	-	11.0	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	4.8	10.7	1.5	11.3	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	2.6	5.3	1.0	5.9	ns
		V_{CC} = 2.7 V	1.0	2.6	4.7	1.0	6.0	ns
		V_{CC} = 3.0 V to 3.6 V	1.1	2.2	4.1	1.1	5.5	ns
t_{en}	enable time	$n\overline{OE}$ to nYn; see Figure 5 [2]						
		V_{CC} = 1.2 V	-	15.0	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	6.2	12.1	1.5	12.7	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	3.5	6.4	1.0	7.1	ns
		V_{CC} = 2.7 V	1.0	3.2	5.8	1.0	7.5	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	2.8	4.6	1.0	6.0	ns
t_{dis}	disable time	$n\overline{OE}$ to nYn; see Figure 5 [2]						
		V_{CC} = 1.2 V	-	10.0	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V	2.5	4.4	8.7	2.5	9.4	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	2.4	4.9	1.0	5.3	ns
		V_{CC} = 2.7 V	1.0	3.2	6.2	1.0	8.0	ns
		V_{CC} = 3.0 V to 3.6 V	1.8	3.1	5.2	1.8	6.5	ns

Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 6.

Symbol	Parameter	Conditions		T_{amb} = –40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
$t_{sk(o)}$	output skew time	V_{CC} = 3.0 V to 3.6 V	[3]	-	-	1.0	-	1.5	ns
C_{PD}	power dissipation capacitance	per flip-flop; V_I = GND to V_{CC}	[4]						
		outputs enabled							
		V_{CC} = 1.65 V to 1.95 V		-	4.8	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	8.3	-	-	-	pF
		V_{CC} = 3.0 V to 3.6 V		-	11.4	-	-	-	pF

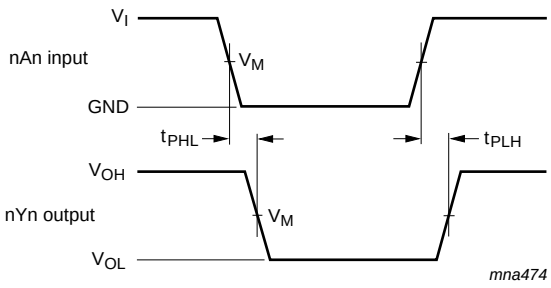
[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.2 V, 1.8 V, 2.5 V, 2.7 V, and 3.3 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZL} and t_{PZH}.
t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

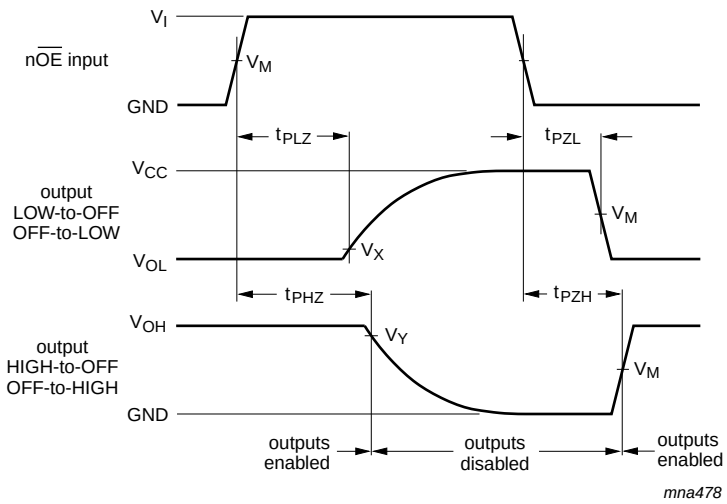
[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz; f_o = output frequency in MHz
C_L = output load capacitance in pF
V_{CC} = supply voltage in Volts
N = number of inputs switching
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs

11. Waveforms



V_M = 1.5 V at $V_{CC} \geq$ 2.7 V.
$V_M = 0.5V_{CC}$ at V_{CC} < 2.7 V.
V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 4. Input (nAn) to output (nYn) propagation delay times



V_M = 1.5 V at $V_{CC} \geq$ 2.7 V

$V_M = 0.5V_{CC}$ at V_{CC} < 2.7 V

$V_X = V_{OL}$ + 0.3 V at $V_{CC} \geq$ 2.7 V

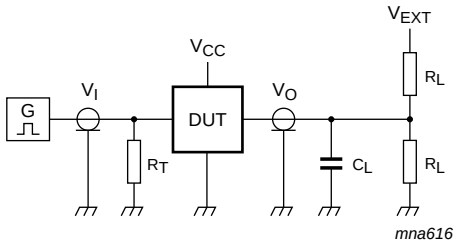
$V_X = V_{OL}$ + 0.1 V at V_{CC} < 2.7 V

$V_Y = V_{OH}$ − 0.3 V at $V_{CC} \geq$ 2.7 V

$V_Y = V_{OH}$ − 0.1 V at V_{CC} < 2.7 V

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. 3-state enable and disable times



Test data is given in Table 8. Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

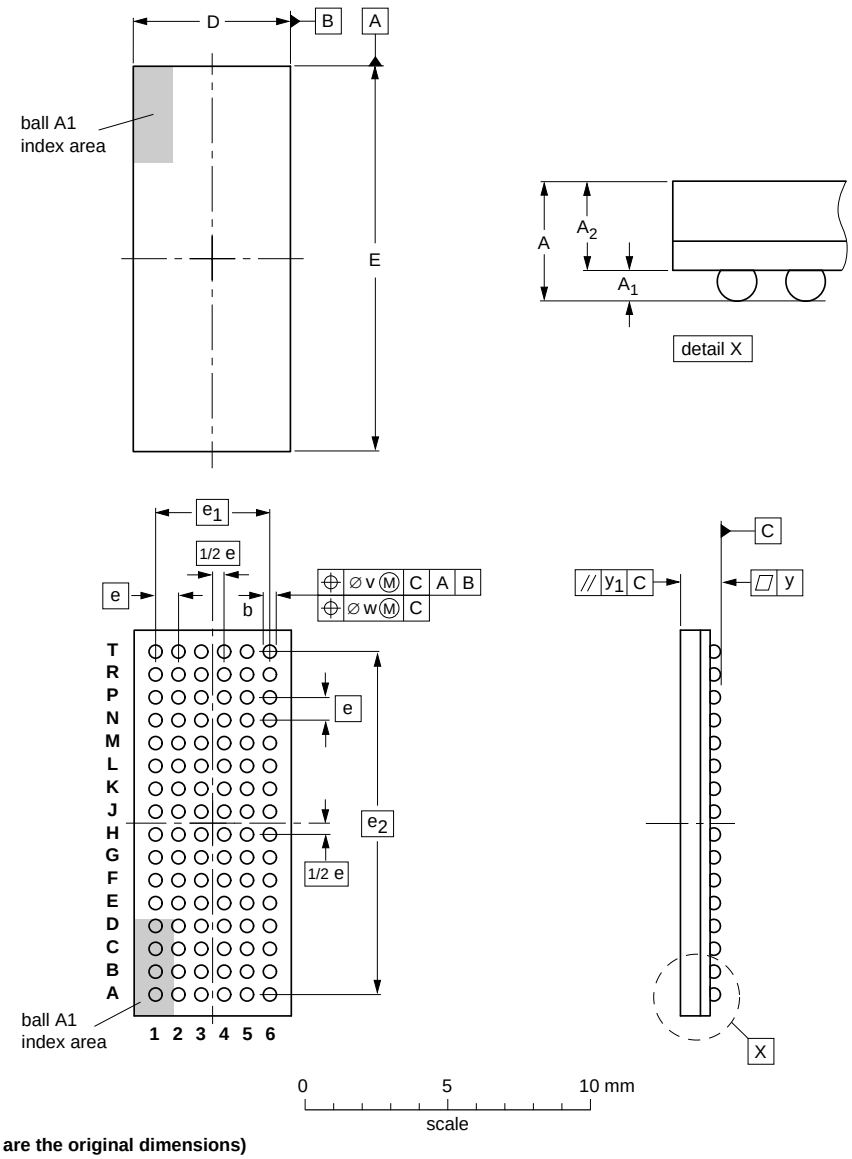
Fig 6. Load circuitry for switching times

Table 8. Test data

Supply voltage	Input		Load		V_{EXT}		
	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PLZ}, t_{PZL}	t_{PHZ}, t_{PZH}
1.2 V	V_{CC}	≤ 2 ns	30 pF	1 kΩ	open	$2 \times V_{CC}$	GND
1.65 V to 1.95 V	V_{CC}	≤ 2 ns	30 pF	1 kΩ	open	$2 \times V_{CC}$	GND
2.3 V to 2.7 V	V_{CC}	≤ 2 ns	30 pF	500 Ω	open	$2 \times V_{CC}$	GND
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	$2 \times V_{CC}$	GND
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	$2 \times V_{CC}$	GND

12. Package outline

LFBGA96: plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 x 5.5 x 1.05 mm SOT536-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	b	D	E	e	e_1	e_2	v	w	y	y_1
mm	1.5	0.41 0.31	1.2 0.9	0.51 0.41	5.6 5.4	13.6 13.4	0.8	4	12	0.15	0.1	0.1	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT536-1						~~00-03-04~~ 03-02-05

Fig 7. Package outline SOT563-1 (LFBGA96)

13. Abbreviations

Table 9. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVCH32244A v.3	20111216	Product data sheet	-	74LVCH32244A v.2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 4, Table 5, Table 6, Table 7 and Table 8: values added for lower voltage ranges.			
74LVCH32244A v.2	20040519	Product specification	-	74LVCH32244A v.1
74LVCH32244A v.1	19991124	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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For sales office addresses, please send an email to: **salesaddresses@nxp.com**

17. Contents

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